



**Ordering Information:**

**Absolute Maximum Ratings**  $T_C = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	80	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	

**Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	$R_{thJC}$	-	-	34	v C/W
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	180	v C/W
Soldering temperature, wavesoldering for 10s	$T_{sold}$	-	-	265	v C

**Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	80			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	1.2		2.5	V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS} = 80V, V_{GS} = 0V$			1.0	$\mu A$
Gate- Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			100	nA
Static Drain-source On Resistance		$V_{GS} = 10V, I_D = 10A$				
		$V_{GS} = 4.5V, I_D = 8A$				
Forward Transconductance	$g_{FS}$	$V_{DS} = 25V, I_D = 4A$				
Source-drain voltage	$V_{SD}$	$I_S = 10A$				

**Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	$C_{iss}$	$f = 1MHz$	-	5300	-	pF
Output capacitance	$C_{oss}$		-	450	-	
Reverse transfer capacitance	$C_{rss}$		-	280	-	

**Gate Charge characteristics( $T_a = 25$  )**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	$Q_g$	$V_{DD} = 30V$	-	72	-	nC
Gate - Source charge	$Q_{gs}$	$I_D = 6A$	-	18	-	
Gate - Drain charge	$Q_{gd}$	$V_{GS} = 10V$	-	21	-	

Note: Pulse Test :

Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate



Fig.1 Gate-Charge Characteristics

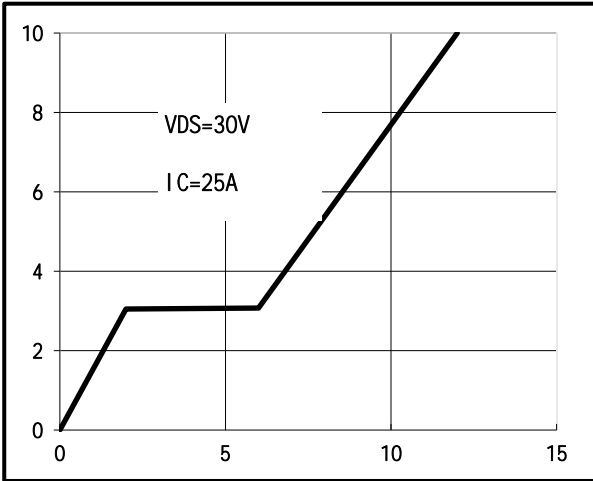


Fig.2 Capacitance Characteristics

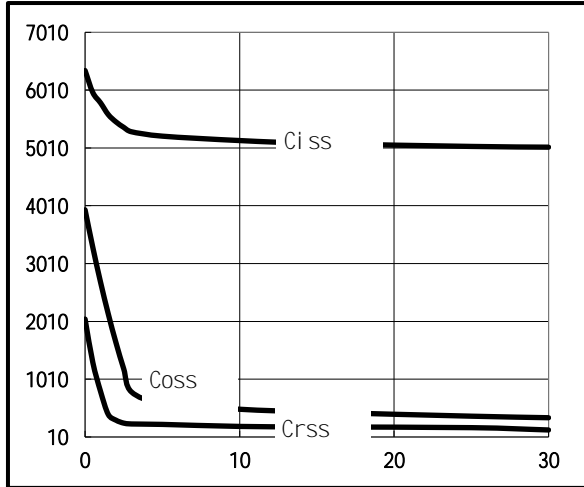


Fig.3 Power Dissipation

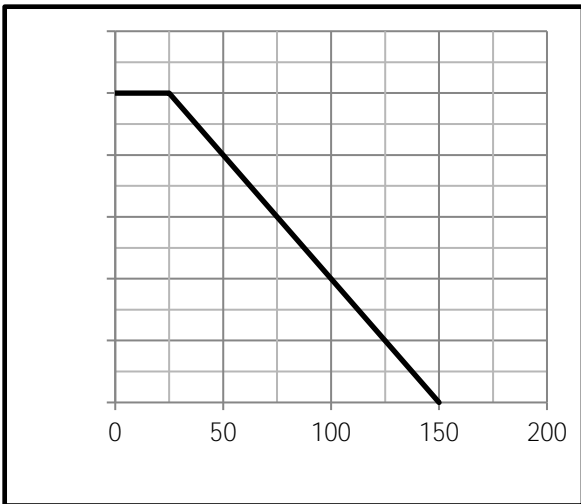


Fig.4 Typical output Characteristics

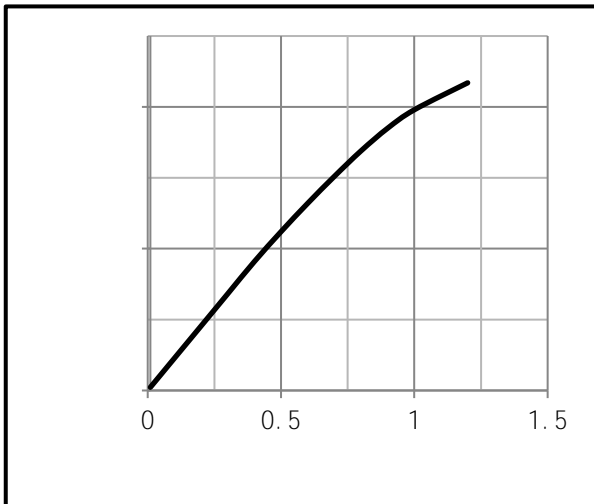


Fig.5 Threshold Voltage V.S Junction Temperature

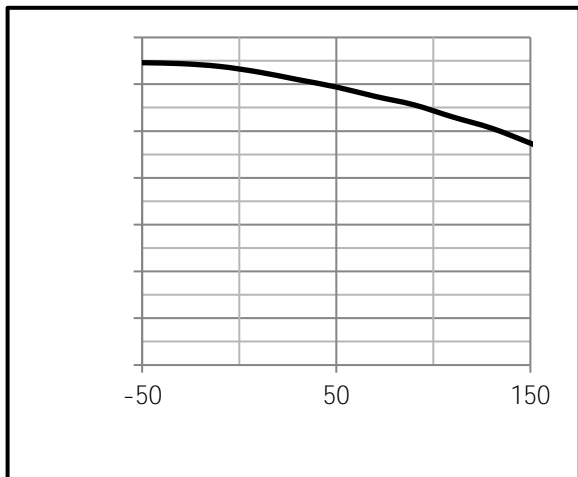
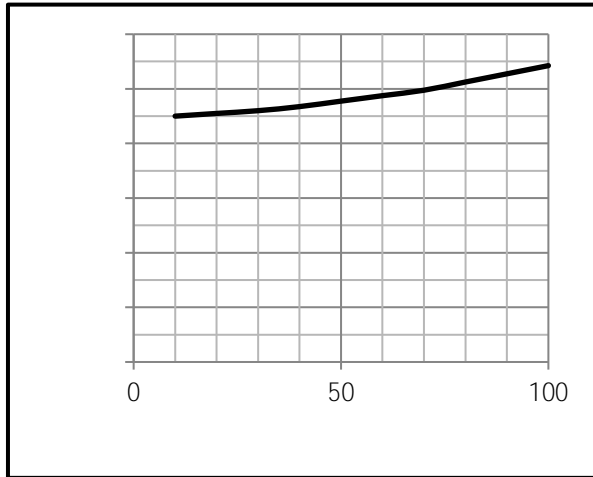


Fig.6 Resistance V.S Drain Current



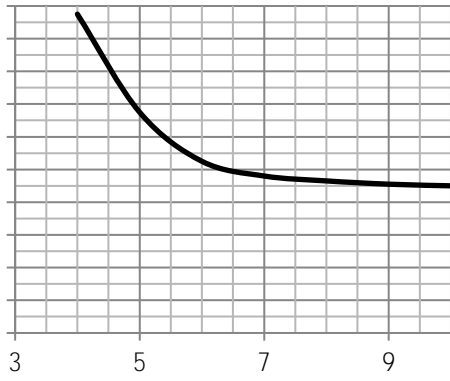


Fig.9 Switching Time Measurement Circuit

Fig.10 Gate Charge Waveform

Fig.11 Switching Time Measurement Circuit

Fig.12 Gate Charge Waveform



Dimensions(SOP8)

Unit mm

SYMBOL	min	TYP	max	SYMBOL	min		max
A	4.80		5.00	C	1.30		1.50
A1	0.37		0.47	C1	0.55		0.75
A2		1.27		C2	0.55		0.65
A3		0.41		C3	0.05		0.20
B	5.80		6.20	C4	0.19	0.20	0.23
B1	3.80		4.00	D		1.05	
B2		5.00		D1	0.40		0.62

